

TOSHIBA

1SS154

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS154

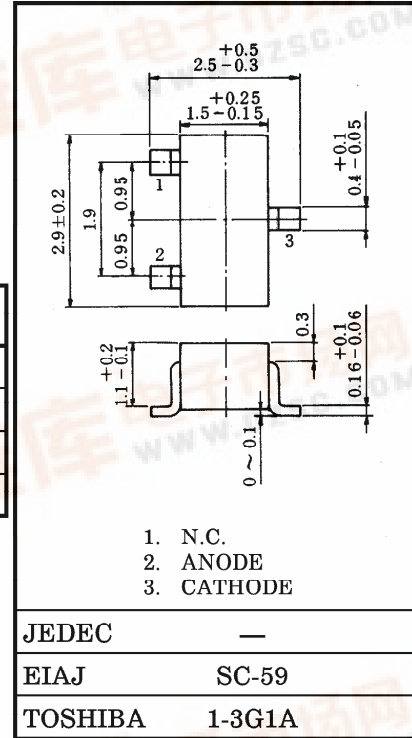
UHF~S BAND MIXER/DETECTOR APPLICATIONS

Unit in mm

- Small Package.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V _R	6	V
Forward Current	I _F	30	mA
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-30~125	°C



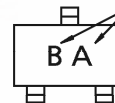
Weight : 0.012g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V _R	I _R = 10 μA	6	—	—	V
Reverse Current	I _R	V _R = 5V	—	—	0.5	μA
Forward Voltage	V _{F(1)}	I _F = 0.1mA	—	—	0.35	V
Forward Voltage	V _{F(2)}	I _F = 10mA	—	0.5	—	V
Total Capacitance	C _T	V _R = 0, f = 1MHz	—	0.8	—	pF

Marking

Type Name



961001FAA2

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